

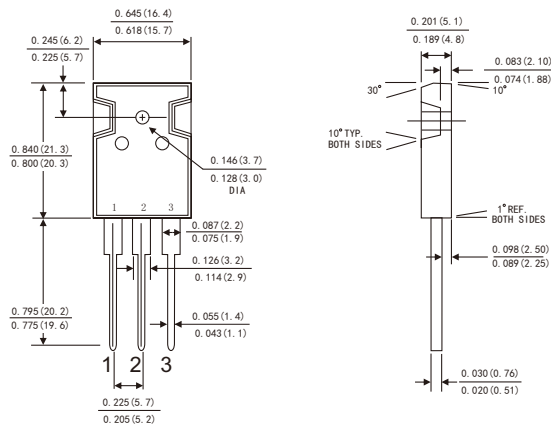
DESCRIPTION

SiC Schottky Diode has no switching loss, provides improved system efficiency against Si diodes by utilizing new semiconductor material-Silicon Carbide, enables higher operating frequency, and helps increasing power density and reduction of system size /cost. Its high reliability ensures robust operation during surge or over_voltage conditions.

FEATURES

- Max Junction Temperature 175° C
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery

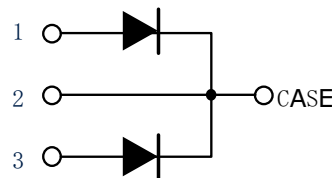
TO-247AB



Dimensions in inches and (millimeters)

MECHANICAL DATA

- Case: JEDEC TO-247AB
- Molding compound meets UL94V-0 flammability rating
- Terminals: Lead solderable per J-STD-002 and JESD22-B102
- Polarity: As marked
- Mounting Torque: 10 in-lbs maximum



TYPICAL APPLICATIONS

- General Purpose
- SMPS, Solar inverter, UPS
- Power Switching Circuits

KEY PERFORMANCE AND PACKAGE PARAMETERS (leg/device)

Type	V _{DC}	I _F	Qc	T _{j,max}	Package
SC20120PT	1200V	10A/20A	30nC/60nC	175°C	TO-247AB

RATINGS AND CHARACTERISTIC OF SC20120PT

MAXIMUM RATINGS

(Ratings at 25℃ ambient temperature unless otherwise specified)

Parameter	Symbol	Value (leg/device)	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	1200	V
Continuous Forward Current for $R_{th(j-c)}$	I_F	10/20 ($T_c \leq 140^{\circ}C$) 31/62 ($T_c \leq 25^{\circ}C$)	A
Non-Repetitive Forward Surge Current (Half-Sine Pulse, $t_p=8.3ms$)	$I_{F,SM}$	95/190($T_c=25^{\circ}C$) 85/170($T_c=150^{\circ}C$)	A
I^2t value	$\int i^2t$	37/148 ($T_c=25^{\circ}C$) 30/120 ($T_c=150^{\circ}C$)	A ² S
Diode dv/dt ruggedness($V_R=0\ldots 960V$)	dv/dt	80	V/nS
Power dissipation for $R_{th(j-c,max)}$ ($T_c=25^{\circ}C$)	P_{tot}	150/150	W
Operating junction temperature range	T_j	-55...175	℃
Storage temperature range	T_{stg}	-55...175	℃

THERMAL CHARACTERISTICS (TA=25℃ Unless otherwise noted)

Parameter	Symbol	Value (leg/device)		Unit
		Typ	Max	
Diode thermal resistance junction-case	$R_{th(j-c)}$	0.8/0.6	1.0/0.8	K/W

RATINGS AND CHARACTERISTIC OF SC20120PT

ELECTRICAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Value(leg/device)			Unit
			min	typ	max	
DC blocking voltage	V _{DC}	T _j =25...175°C	1200			V
Diode forward voltage	V _F	IF=10A/20A T _j =25°C IF=10A/20A T _j =125°C IF=10A/20A T _j =175°C		1.7 2.3 2.8	1.9 2.5 3.2	V
Reverse current	I _R	VR=1200V T _j =25°C VR=1200V T _j =125°C VR=1200V T _j =175°C			20/40 100/200 200/400	uA

DYNAMIC CHARACTERISTICS(at T_j=25°C,unless otherwise specified)

Parameter	Symbol	conditions	Value(leg/device)			Unit
			min	typ	max	
Total capacitive charge	Q _c	VR=1200V,IF=10A di/dt=200A/uS T _j =25°C		30/60		nC
Total capacitance	C	V _R =1V,f=1MHz V _R =400V,f=1MHz V _R =800V,f=1MHz T _j =25°C		650/1300 49/98 40/80		pF

RATINGS AND CHARACTERISTIC OF SC20120PT

FIG.1-FORWARD CURRENT DERATING CURVE(device)

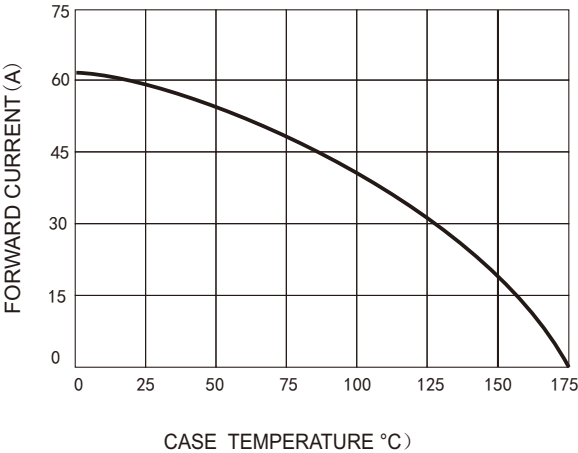


FIG.2-TYPICAL JUNCTION CAPACITANCE(per leg)

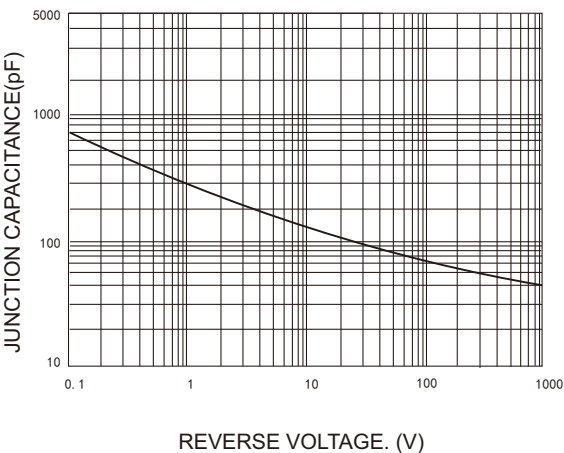


FIG.3-FORWARD CURRENT DERATING CURVE(per leg)

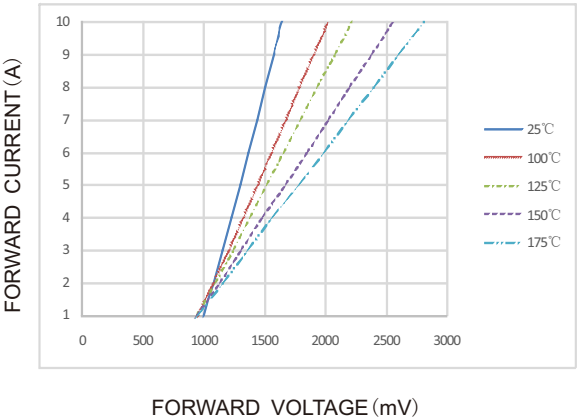
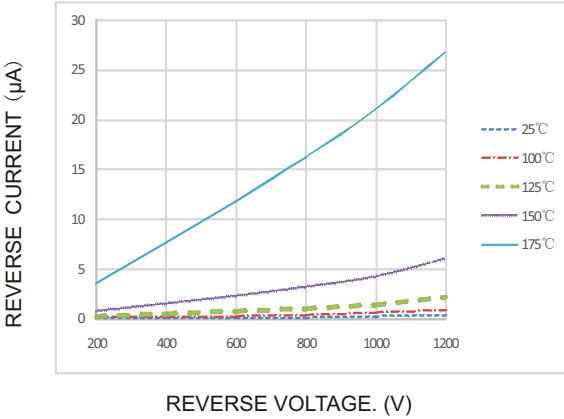


FIG.4-REVERSE CHARACTERISTICS(per leg)



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